

SN65LVDS16, SN65LVP16 SN65LVDS17, SN65LVP17

SLLS625B-SEPTEMBER 2004-REVISED NOVEMBER 2005

2.5-V/3.3-V OSCILLATOR GAIN STAGE/BUFFERS

FEATURES

- Low-Voltage PECL Input and Low-Voltage PECL or LVDS Outputs
- · Clock Rates to 2 GHz
 - 140-ps Output Transition Times
 - 0.11 ps Typical Intrinsic Phase Jitter
 - Less than 630 ps Propagation Delay Times
- 2.5-V or 3.3-V Supply Operation

 2-mm x 2-mm Small-Outline No-Lead Package

APPLICATIONS

- PECL-to-LVDS Translation
- Clock Signal Amplification

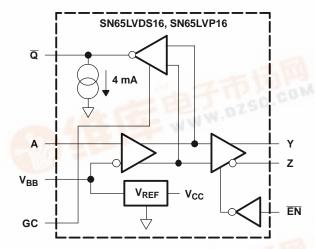
DESCRIPTION

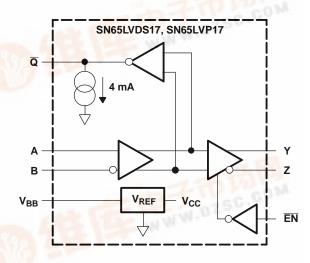
These four devices are high-frequency oscillator gain stages supporting both LVPECL or LVDS on the high gain outputs in 3.3-V or 2.5-V systems. Additionally, provides the option of both single-ended input (PECL levels on the SN65LVx16) and fully differential inputs on the SN65LVx17.

The SN65LVx16 provides the user a Gain Control (GC) for controlling the $\overline{\mathbb{Q}}$ output from 300 mV to 860 mV either by leaving it open (NC), grounded, or tied to V_{CC} . (When left open, the $\overline{\mathbb{Q}}$ output defaults to 575 mV.) The $\overline{\mathbb{Q}}$ on the SN65LVx17 defaults to 575 mV as well.

Both devices provide a voltage reference (V_{BB}) of typically 1.35 V below V_{CC} for use in receiving single-ended PECL input signals. When not used, V_{BB} should be unconnected or open.

All devices are characterized for operation from -40°C to 85°C.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS(1)

INPUT	OUTPUT	GAIN CONTROL	BASE PART NUMBER	PART MARKING
Single-ended	LVDS	Yes	SN65LVDS16	EL
Single-ended	LVPECL	Yes	SN65LVP16	EK
Differential	LVDS	No	SN65LVDS17	EN
Differential	LVPECL	No	SN65LVP17	EM

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1)

		UNIT
V_{CC}	Supply voltage ⁽²⁾	–0.5 V to 4 V
V_{I}	Input voltage	-0.5 V to V _{CC} + 0.5 V
V_{O}	Output voltage	-0.5 V to V _{CC} + 0.5 V
Io	V _{BB} output current	±0.5 mA
	HBM electrostatic discharge (3)	±3 kV
	CDM electrostatic discharge (4)	±1500 V
	Continuous power dissipation	See Power Dissipation Ratings Table

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATINGS

PACKAGE	CIRCUIT BOARD MODEL	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C ⁽¹⁾	T _A = 85°C POWER RATING
DRF	Low-K ⁽²⁾	403 mW	4.0 mW/°C	161 mW
DKF	High-K ⁽³⁾	834 mW	8.3 mW/°C	333 mW

This is the inverse of the junction-to-ambient thermal resistance when board-mounted and with no air flow.

THERMAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	VALUE	UNIT
θ_{JB}	Junction-to-board thermal resistance			93.3	°C/W
θ_{JC}	Junction-to-case thermal resistance			101.7	C/VV
		Tomical	V _{CC} = 3.3 V, T _A = 25°C, 2 GHz, LVDS	132	
_	Davisa navva dissination	Typical	V _{CC} = 3.3 V, T _A = 25°C, 2 GHz, LVPECL	83	\^/
P_D	Device power dissipation	Maximum	V _{CC} = 3.6 V, T _A = 85°C, 2 GHz, LVDS	173	mW
		Maximum	V _{CC} = 3.6 V, T _A = 85°C, 2 GHz, LVPECL	108	

All voltage values, except differential voltages, are with respect to network ground see Figure 1).

Tested in accordance with JEDEC Standard 22, Test Method A114-A-7 Tested in accordance with JEDEC Standard 22, Test Method C101

In accordance with the Low-K thermal metric definitions of EIA/JESD51-3.

In accordance with the High-K thermal metric definitions of EIA/JESD51-7.



RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage		2.375	2.5 or 3.3	3.6	V
V_{IC}	Common-mode input voltage (V _{IA} + V _{IB})/2	SN65LVDS17 or SN65LVP17	1.2		$V_{CC} - (V_{ID}/2)$	V
$ V_{ID} $	Differential input voltage magnitude V _{IA} - V _{IB}	SN65LVDS17 or SN65LVP17	0.08		1	V
V	High level input voltage to EN	EN	2		V _{CC}	V
V _{IH}	High-level input voltage to EN	SN65LVDS16 or SN65LVP16	V _{CC} - 1.17		V _{CC} - 0.44	V
V	Low level input veltage to EN	EN	0		8.0	٧
V _{IL}	Low-level input voltage to EN	SN65LVDS16 or SN65LVP16	V _{CC} - 2.25		V _{CC} - 1.52	V
Io	Output current to V _{BB}		-400 ⁽¹⁾		400	μA
R_L	Differential load resistance,		90		132	Ω
T_A	Operating free-air temperature	-40		85	°C	

⁽¹⁾ The algebraic convention, where the least positive (more negative) value is designated minimum, is used in this data sheet.

ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
	Complex company	$R_L = 100 \ \Omega, \ \overline{EN} \ \text{at 0 V},$ Other inputs open		40	48	Λ
Icc	Supply current	Outputs unloaded, EN at 0 V, Other inputs open		25	30	mA
V_{BB}	Reference voltage ⁽²⁾	$I_{BB} = -400 \mu A$	V _{CC} - 1.44	V _{CC} - 1.35	V _{CC} - 1.25	V
I _{IH}	High-level input current, EN	V _I = 2 V	-20		20	
I _{IAH} or I _{IBH}	High-level input current, A or B	$V_I = V_{CC}$	-20		20	
I _{IL}	Low-level input current, EN	V _I = 0.8 V	-20		20	μA
I _{IAL} or I _{IBL}	Low-level input current, A or B	V _I = GND	-20		20	
SN65LVDS1	6/17 Y AND Z OUTPUT CHARACTERI	STICS				
V _{OD}	Differential output voltage magnitude, V _{OY} - V _{OZ}		247	340	454	mV
$\Delta V_{OD} $	Change in differential output voltage magnitude between logic states	See Figure 1 and Figure 2			50	IIIV
V _{OC(SS)}	Steady-state common-mode output voltage (see Figure 3)		1.125		1.375	V
$\Delta V_{OC(SS)}$	Change in steady-state common- mode output voltage between logic states	See Figure 3	-50		50	mV
V _{OC(PP)}	Peak-to-peak common-mode output voltage	_		50	100	
I _{OYZ} or I _{OZZ}	High-impedance output current	$\overline{\text{EN}}$ at V_{CC} , $V_{\text{O}} = 0 \text{ V or } V_{\text{CC}}$	-1		1	μA
I _{OYS} or I _{OZS}	Short-circuit output current	EN at 0 V, V _{OY} or V _{OZ} = 0 V	-62		62	
I _{OS(D)}	Differential short-circuit output current, I _{OY} - I _{OZ}	EN at 0 V, V _{OY} = V _{OZ}	-12		12	mA

⁽¹⁾ Typical values are at room temperature and with a V_{CC} of 3.3 V. (2) Single-ended input operation is limited to $V_{CC} \ge 3.0$ V.

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ELECTRICAL CHARACTERISTICS (continued)

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
SN65LVP16	/17 Y AND Z OUTPUT CHARACTERIS	TICS				
V _{OYH} or V _{OZH}	High-level output voltage	3.3 V; 50 Ω from Y and Z	V _{CC} - 1.05		V _{CC} - 0.82	
V _{OYL} or V _{OZL}	Low-level output voltage	to V _{CC} - 2 V	V _{CC} - 1.83		V _{CC} - 1.57	V
V _{OYL} or V _{OZL}	Low-level output voltage	2.5 V; 50 Ω from Y and Z to V _{CC} - 2 V	V _{CC} - 1.88		V _{CC} - 1.57	V
V _{OD}	Differential output voltage magnitude, $ V_{OH} - V_{OL} $		0.6	0.8	1	
I _{OYZ} or I _{OZZ}	High-impedance output current	$\overline{\text{EN}}$ at V_{CC} , $V_{\text{O}} = 0$ V or V_{CC}	-1		1	μA
Q OUTPUT	CHARACTERISTICS (see Figure 1)					
V _{OH}	High-level output voltage	No load		V _{CC} - 0.94		V
		GC Tied to GND, No load		V _{CC} - 1.22		
V_{OL}	Low-level output voltage	GC Open, No load		V _{CC} - 1.52		V
		GC Tied to V _{CC} , No load		V _{CC} - 1.82		
		GC Tied to GND		300		
$V_{O(pp)}$	Peak-to-peak output voltage	GC Open		575		mV
		GC Tied to V _{CC}		860		

SWITCHING CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
	Dropogation delay time to or t	A to Q			340	460	
t _{PD}	Propagation delay time, t _{PLH} or t _{PHL}	D to Y or Z	See Figure 4		460	630	ps
t _{SK(P)}	Pulse skew, t _{PLH} t _{PHL}					20	
	Part-to-part skew ⁽²⁾		V _{CC} = 3.3 V			80	no
t _{SK(PP)}	Fait-to-part skew -/		V _{CC} = 2.5 V			130	ps
t _r	20%-to-80% differential signal rise tin	me	See Figure 4		85	140	ps
t _f	20%-to-80% differential signal fall tin	ne	See Figure 4		85	140	ps
t _{jit(per)}	RMS period jitter ⁽³⁾		2-GHz 50%-duty-cycle square-wave input,		2	3	20
t _{jit(cc)}	Peak cycle-to-cycle jitter ⁽⁴⁾		See Figure 5		15	23	ps
t _{jit(ph)}	Intrinsic phase jitter		2 GHz		0.11		ps
t _{PHZ}	Propagation delay time, high-level-to-high-impedance output					30	
t _{PLZ}	Propagation delay time, low-level-to-high-impedance output		Con Figure C			30	
t _{PZH}	Propagation delay time, high-impedance-to-high-level output		See Figure 6			30	ns
t _{PZL}	Propagation delay time, high-impedance-to-low-level output					30	

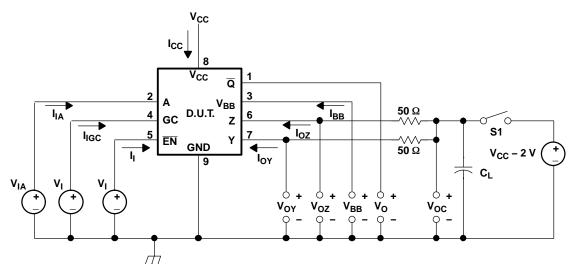
 ⁽¹⁾ Typical values are at room temperature and with a V_{CC} of 3.3 V.
 (2) Part-to-part skew is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

Period jitter is the deviation in cycle time of a signal with respect to the ideal period over a random sample of 100,000 cycles.

Cycle-to-cycle jitter is the variation in cycle time of a signal between adjacent cycles, over a random sample of 1,000 adjacent cycle pairs.

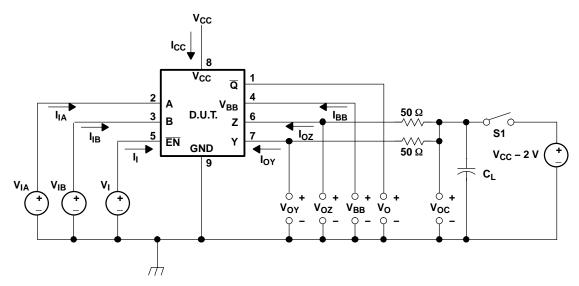


PARAMETER MEASUREMENT INFORMATION



- (1) C_L is the instrumentation and test fixture capacitance.
- (2) S1 is open for the SN65LVDS16 and closed for the SN65LVP16.

Figure 1. Output Voltage Test Circuit and Voltage and Current Definitions for LVDS/LVP16



- (1) C₁ is the instrumentation and test fixture capacitance.
- (2) S1 is open for the SN65LVDS17 and closed for the SN65LVP17.

Figure 2. Output Voltage Test Circuit and Voltage and Current Definitions for LVDS/LVP17

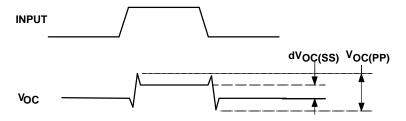


Figure 3. V_{OC} Definitions



PARAMETER MEASUREMENT INFORMATION (continued)

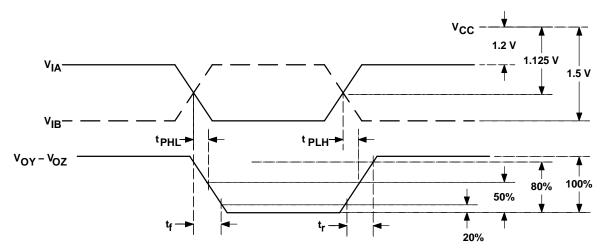


Figure 4. Propagation Delay and Transition Time Test Waveforms

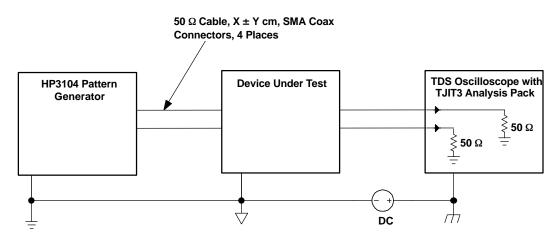


Figure 5. Jitter Measurement Setup



PARAMETER MEASUREMENT INFORMATION (continued)

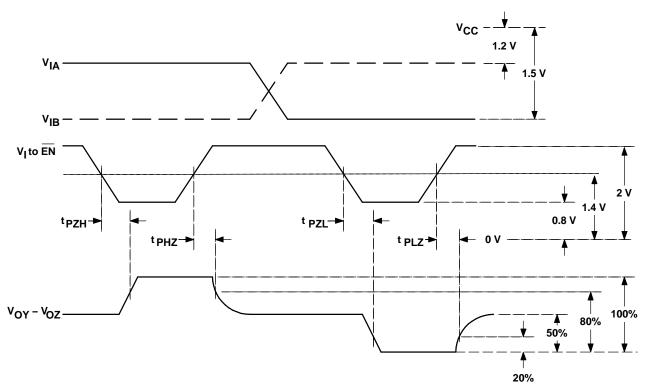


Figure 6. Enable and Disable Time Test Waveforms



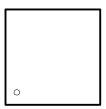
DEVICE INFORMATION

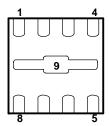
FUNCTION TABLE

SN65LVDS16, SN65LVP16 ⁽¹⁾				SN65LVDS17, SN65LVP17 ⁽¹⁾						
Α	EN	Q	Y	Z	Α	В	EN	Q	Υ	Z
Н	L	L	Н	L	Н	Н	L	?	?	?
L	L	Н	L	Н	L	Н	L	Н	L	Н
Х	Н	?	Z	Z	Н	L	L	L	Н	L
Open	L	?	?	?	L	L	L	?	?	?
Х	Open	?	?	?	Х	Х	Н	?	Z	Z
					Open	Open	L	?	?	?
					Х	Х	Open	?	?	?

(1) H = high, L = low, Z = high impedance, ? = indeterminate

DRF PACKAGE TOP VIEW





BOTTOM VIEW

Package Pin Assignments - Numerical Listing

SN65LVDS1	6, SN65LVP16	SN65LVDS17	, SN65LVP17
PIN	SIGNAL	PIN	SIGNAL
1	Q	1	Q
2	A	2	A
3	V _{BB}	3	В
4	GC	4	V_{BB}
5	EN	5	EN
6	Z	6	Z
7	Y	7	Υ
8	V _{CC}	8	V_{CC}
9	GND	9	GND

SUPPLY CURRENT



TYPICAL CHARACTERISTICS

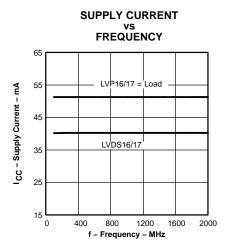


Figure 7.

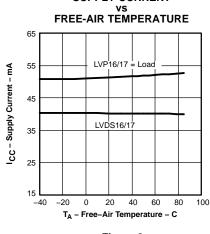


Figure 8.

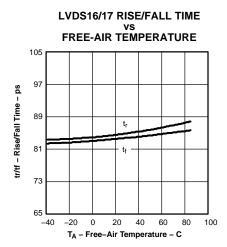


Figure 9.

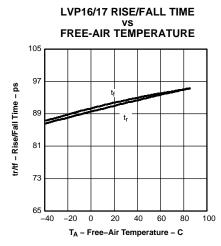


Figure 10.

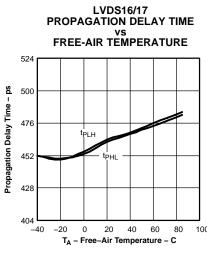
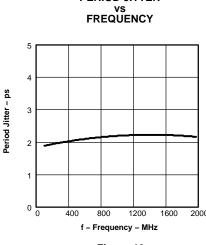
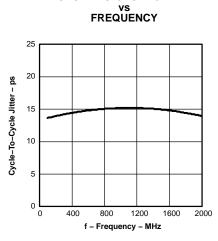


Figure 11.



PERIOD JITTER

Figure 12.

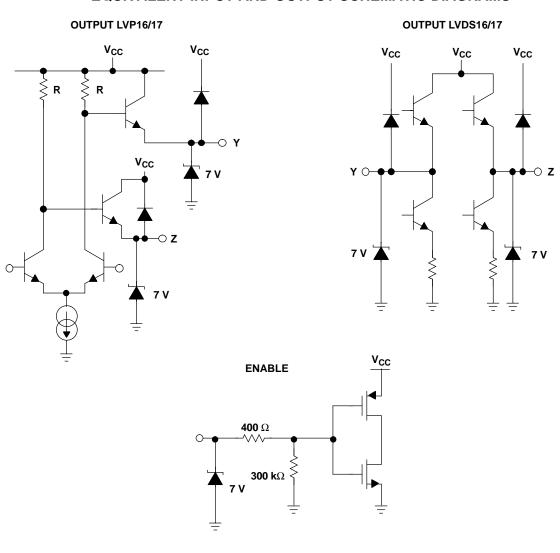


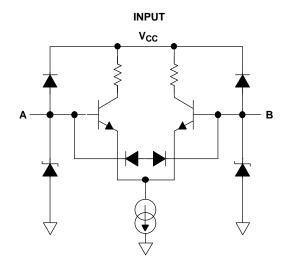
CYCLE-TO-CYCLE JITTER

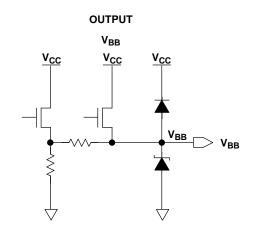
Figure 13.



EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS







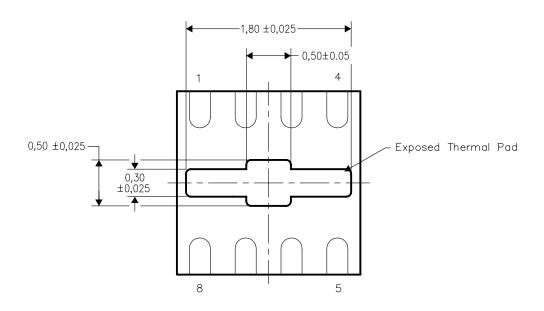
THERMAL PAD MECHANICAL DATA DRF (S-PDSO-N8)

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB), the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to a ground plane or special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No—Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No—Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions





nn 17-Nov-2005

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN65LVDS16DRFR	ACTIVE	SON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS16DRFRG4	ACTIVE	SON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS16DRFT	ACTIVE	SON	DRF	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS16DRFTG4	ACTIVE	SON	DRF	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS17DRFR	ACTIVE	SON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS17DRFRG4	ACTIVE	SON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS17DRFT	ACTIVE	SON	DRF	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVDS17DRFTG4	ACTIVE	SON	DRF	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVP16DRFR	ACTIVE	SON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVP16DRFRG4	ACTIVE	SON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVP16DRFT	ACTIVE	SON	DRF	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVP16DRFTG4	ACTIVE	SON	DRF	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVP17DRFR	ACTIVE	SON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVP17DRFRG4	ACTIVE	SON	DRF	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVP17DRFT	ACTIVE	SON	DRF	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65LVP17DRFTG4	ACTIVE	SON	DRF	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): Ti's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



PACKAGE OPTION ADDENDUM

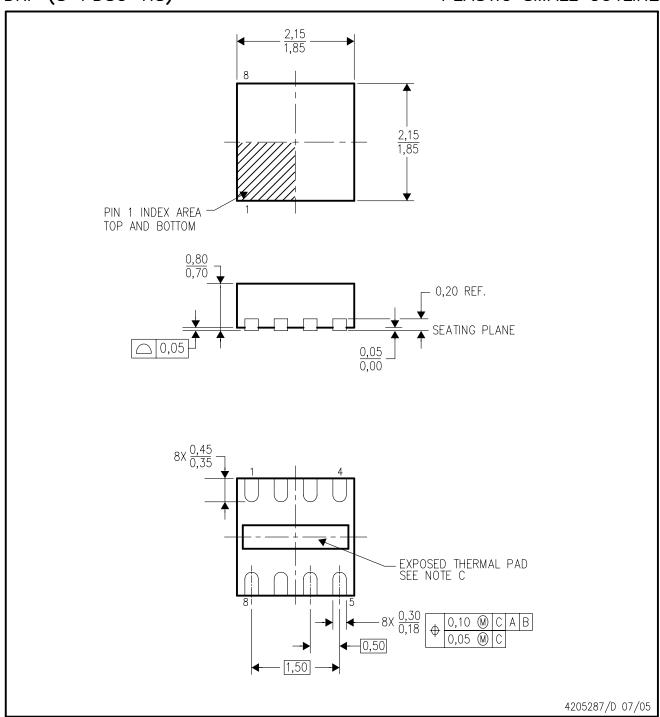
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DRF (S-PDSO-N8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- The Package thermal pad must be soldered to the board for thermal and mechanical performance. See product data sheet for details regarding the exposed thermal pad dimensions.
- D. Falls within JEDEC MO-229.



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